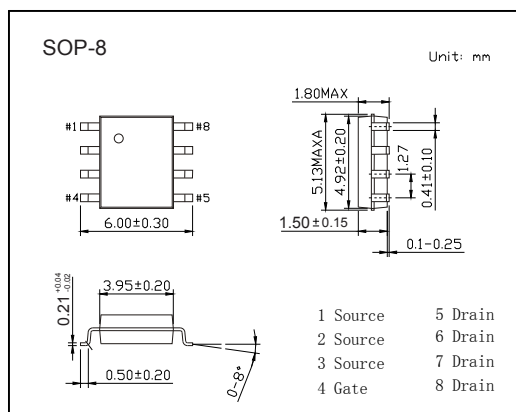
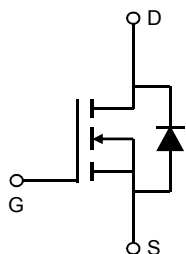


■ Features

- $V_{DS} (V) = 30V$
- $I_D = 14A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 7.5m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 15.5m\Omega$ ($V_{GS} = 4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_A = 25^\circ C$	I_D	14	A
	$T_A = 70^\circ C$		10.4	
Pulsed Drain Current		I_{DM}	100	
Avalanche Current		I_{AS}	22	
Avalanche energy	$L = 0.1mH$	E_{AS}	24	mJ
Power Dissipation	$T_A = 25^\circ C$	P_D	3.1	W
	$T_A = 70^\circ C$		2	
Thermal Resistance.Junction- to-Ambient	$t \leq 10s$	R_{thJA}	40	$^\circ C/W$
	Steady-State		75	
Thermal Resistance.Junction- to-Lead		R_{thJL}	24	
Junction Temperature		T_J	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μ A, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μ A
		V _{DS} =30V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} = $\pm$ 20V			$\pm$ 100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 μ A	1.5		2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =14A		7.5		m Ω
		V _{GS} =10V, I _D =14A T _J =125°C		12		
		V _{GS} =4.5V, I _D =10A		15.5		
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =5V	100			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =14A		45		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz	610		910	pF
Output Capacitance	C _{oss}		88		160	
Reverse Transfer Capacitance	C _{rss}		40		100	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.8		2.4	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =12A	11		17	nC
Total Gate Charge (4.5V)			5		8	
Gate Source Charge			1.9		2.9	
Gate Drain Charge			1.8		4.2	
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{DS} =15V, R _L =1.25 Ω , R _{GEN} =3 Ω		4.4		ns
Turn-On Rise Time	t _r			9		
Turn-Off DelayTime	t _{d(off)}			17		
Turn-Off Fall Time	t _f			6		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 12A, di/dt= 500A/us	5.6		8	nC
Body Diode Reverse Recovery Charge	Q _{rr}		6.4		9.6	
Maximum Body-Diode Continuous Current	I _S				4	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μ s pulses, duty cycle 0.5% max.

■ Marking

Marking	4410
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Typical Characteristics

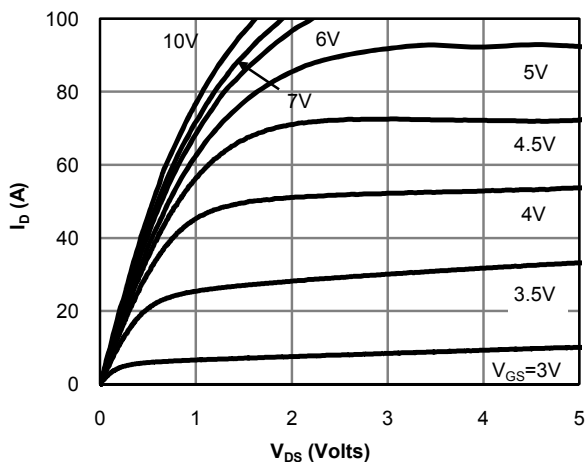


Fig 1: On-Region Characteristics (Note E)

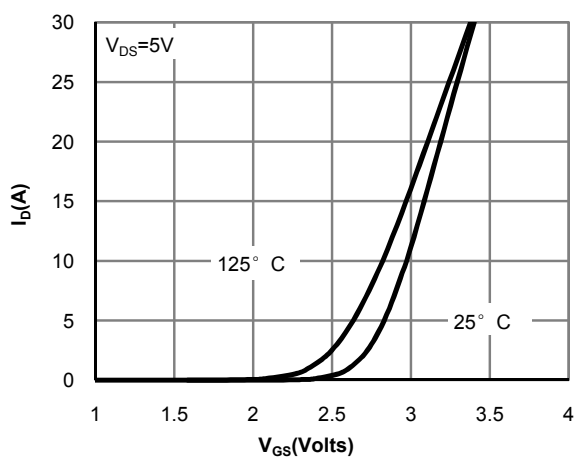


Figure 2: Transfer Characteristics (Note E)

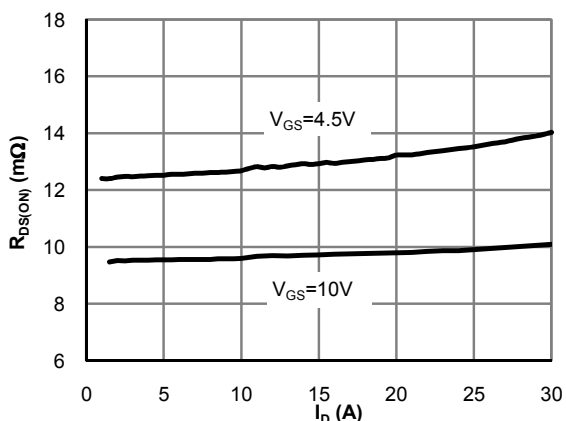


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

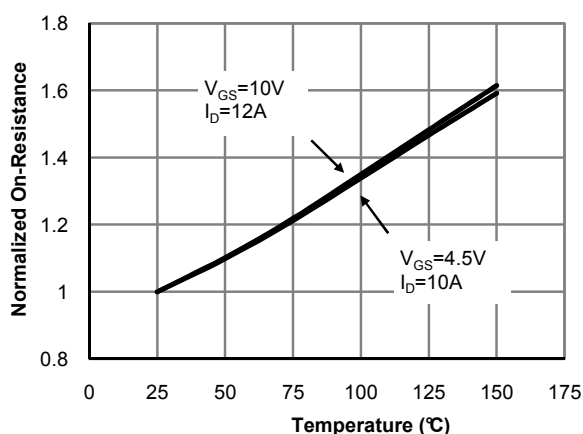


Figure 4: On-Resistance vs. Junction Temperature (Note E)

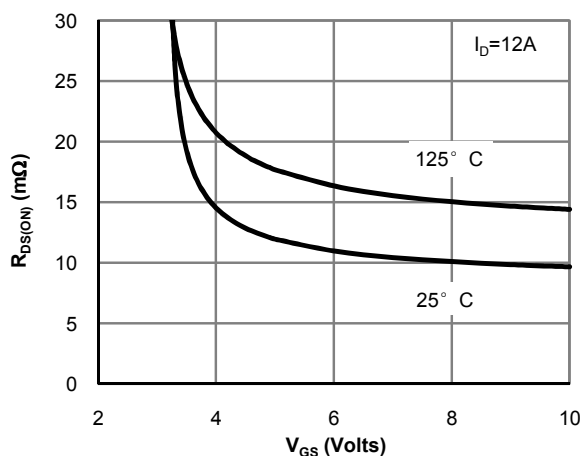


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

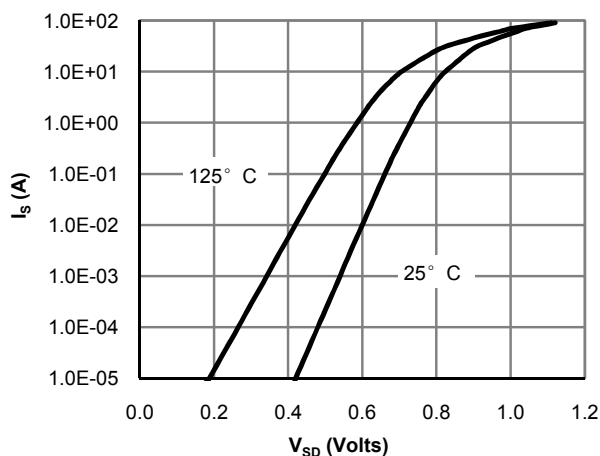


Figure 6: Body-Diode Characteristics (Note E)

Typical Characteristics

